



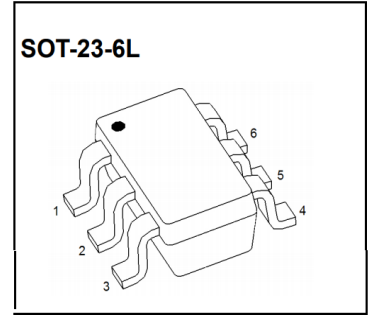
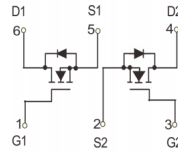
Plastic-Encapsulate MOSFETS

N-channel MOSFET

Features

- High density cell design for low $R_{DS(ON)}$
- Voltage controlled small signal switching
- High saturation current capability
- High speed switching

MARKING: 7002

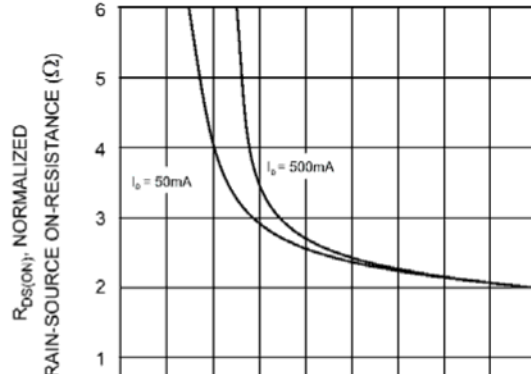
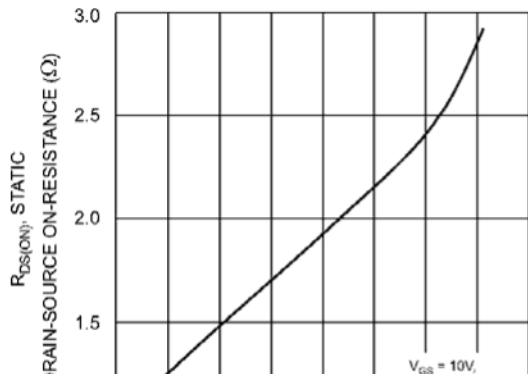
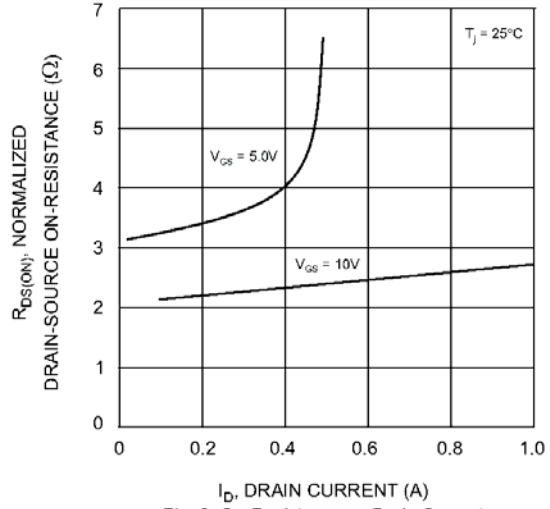
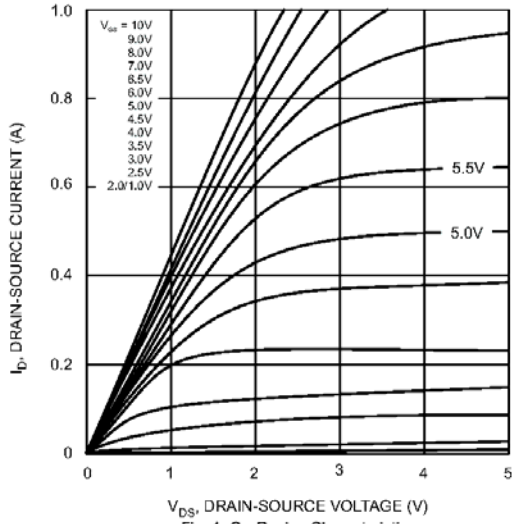


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage ($R_{GS} \leq 1M\Omega$)	V_{DGR}	60	V
Gate-Source Voltage -Continuous -Non Repetitive ($t_p < 50\ \mu s$)	V_{GSS}	± 20 ± 40	V
Maximum Drain Current -Continuous -Pulsed	I_D	115 800	mA
Total Power Dissipation	P_{tot}	200	mW
Operating and Storage Temperature Range	T_J, T_s	- 55 to + 150	$^\circ\text{C}$

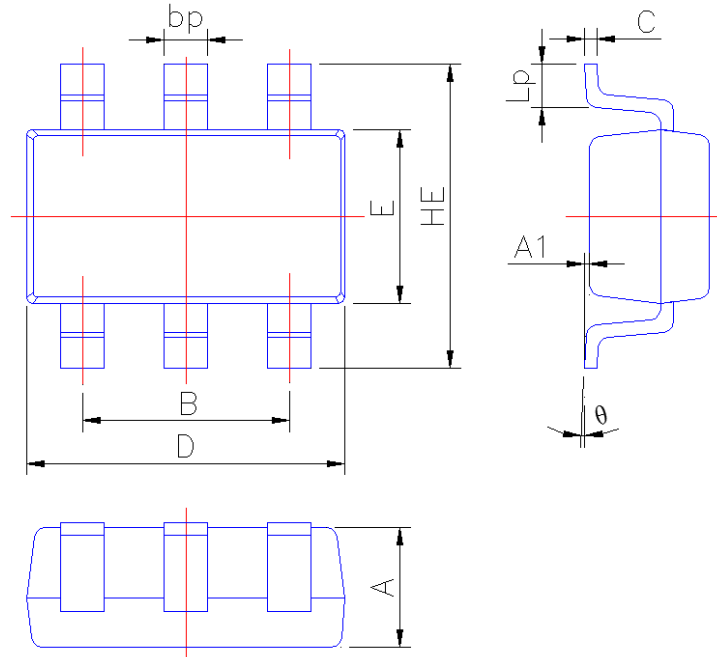
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Drain Source Breakdown Voltage at $I_D = 10\ \mu A$	BV_{DSS}	60	-	V
Zero Gate Voltage Drain Current at $V_{DS} = 60\text{ V}$	I_{DSS}	-	1	μA
Gate-Body Leakage Current at $V_{GS} = \pm 20\text{ V}$	$\pm I_{GSS}$	-	100	nA
Gate Threshold Voltage at $V_{DS} = V_{GS}, I_D = 250\ \mu A$	$V_{GS(th)}$	1	2.5	V
On-State Drain Current at $V_{GS} = 10\text{ V}, V_{DS} = 7.5\text{ V}$	$I_{D(ON)}$	500	-	mA
Drain-Source On-Voltage at $V_{GS} = 10\text{ V}, I_D = 500\text{ mA}$ at $V_{GS} = 5\text{ V}, I_D = 50\text{ mA}$	$V_{DS(ON)}$	- -	3.75 1.5	V V
Static Drain-Source On-Resistance at $V_{GS} = 10\text{ V}, I_D = 500\text{ mA}$	$R_{DS(ON)}$	-	7.5	Ω
Forward Transconductance at $V_{DS} = 10\text{ V}, I_D = 200\text{ mA}$	g_{FS}	80	-	mS
Input Capacitance at $V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	C_{iss}	-	50	pF
Output Capacitance at $V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	C_{oss}	-	25	pF
Reverse Transfer Capacitance at $V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	C_{rss}	-	5	pF
Turn-On Time at $V_{DD} = 30\text{ V}, R_L = 150\ \Omega, I_D = 0.2\text{ A}, V_{GS} = 10\text{ V}, R_{GEN} = 25\ \Omega$	t_{on}	-	20	ns
Turn-Off Time at $V_{DD} = 30\text{ V}, R_L = 150\ \Omega, I_D = 0.2\text{ A}, V_{GS} = 10\text{ V}, R_{GEN} = 25\ \Omega$	t_{off}	-	20	ns





SOT-23-6L Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	1.05	1.20
A1	0.010	0.100
B	1.80	2.00
bp	0.35	0.50
C	0.09	0.15
D	2.80	3.00
E	1.50	1.70
HE	2.60	3.00
Lp	0.25	0.55
θ	2°	6°